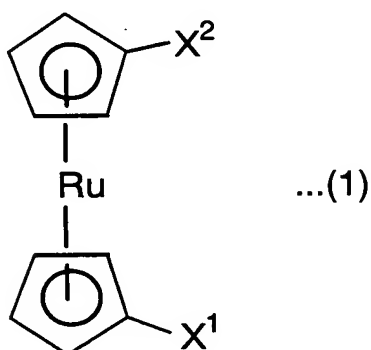


## CLAIMS

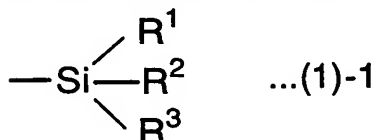
1. (Amended) A ruthenium compound for chemical vapor deposition which is at least one compound selected from the group consisting of a compound represented by the following

5 formula (1):



wherein X<sup>1</sup> and X<sup>2</sup> are each independently a hydrogen atom, fluorine atom, trifluoromethyl group, pentafluoroethyl

10 group or group represented by the following formula (1)-1:



wherein R<sup>1</sup>, R<sup>2</sup> and R<sup>3</sup> are each independently a hydrocarbon group having 1 to 10 carbon atoms,

15 with the proviso that X<sup>1</sup> and X<sup>2</sup> cannot be hydrogen atoms at the same time,

a compound represented by the following formula (2):



wherein R<sup>4</sup> is a trifluoromethyl group or hydrocarbon group having 1 to 10 carbon atoms, and three R<sup>4</sup>'s may be the same or different,

20 and a compound represented by the following formula (4):



wherein Y is a cyclopentadienyl, cyclohexadienyl, cycloheptadienyl, cyclooctadienyl, butadienyl or

25

ART. 19

2,3-dimethyl-1,3-butadienyl group, L is a carbonyl group,  
methyl group or ethenyl group, n is an integer of 1 to 4,  
and m is an integer of 0 to 2, with the proviso that  $n + m$   
is 3 or 4, and two L's may be the same or different when m  
5 is 2.

2. A process for producing a metal ruthenium film from  
the ruthenium compound of claim 1 by chemical vapor  
deposition.